

RJK60S3DPP-E0

600V - 12A - SJ MOS FET
High Speed Power Switching

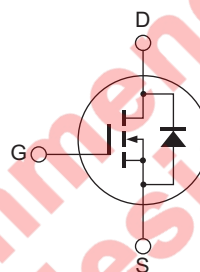
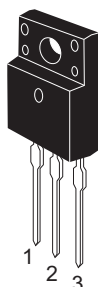
R07DS0637EJ0300
Rev.3.00
Oct 12, 2012

Features

- Superjunction MOSFET
- Low on-resistance
 $R_{DS(on)} = 0.35 \Omega$ typ. (at $I_D = 6 A$, $V_{GS} = 10 V$, $T_a = 25^\circ C$)
- High speed switching
 $t_f = 21 ns$ typ. (at $I_D = 6 A$, $V_{GS} = 10 V$, $R_L = 50 \Omega$, $R_g = 10 \Omega$, $T_a = 25^\circ C$)

Outline

RENESAS Package code: PRSS0003AG-A
(Package name: TO-220FP)



1. Gate
2. Drain
3. Source

Absolute Maximum Ratings

($T_a = 25^\circ C$)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DS}	600	V
Gate to source voltage	V_{GS}	+30, -20	V
Drain current	$T_C = 25^\circ C$ I_D ^{Note1,2}	12.0	A
	$T_C = 100^\circ C$ I_D ^{Note1,2}	7.6	A
Drain peak current	I_D (pulse) ^{Note1}	24	A
Body-drain diode reverse drain current	I_{DR} ^{Note1}	12	A
Body-drain diode reverse drain peak current	I_{DR} (pulse) ^{Note1}	24	A
Avalanche current	I_{AP} ^{Note3}	3	A
Avalanche energy	E_{AR} ^{Note3}	0.49	mJ
Channel dissipation	P_{ch} ^{Note4}	27.7	W
Channel to case thermal impedance	θ_{ch-c}	4.5	$^\circ C/W$
Channel temperature	T_{ch}	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

- Notes: 1. Limited by T_{ch} max.
2. Maximum duty cycle $D = 0.75$
3. $ST_{ch} = 25^\circ C$, $T_{ch} \leq 150^\circ C$
4. Value at $T_C = 25^\circ C$

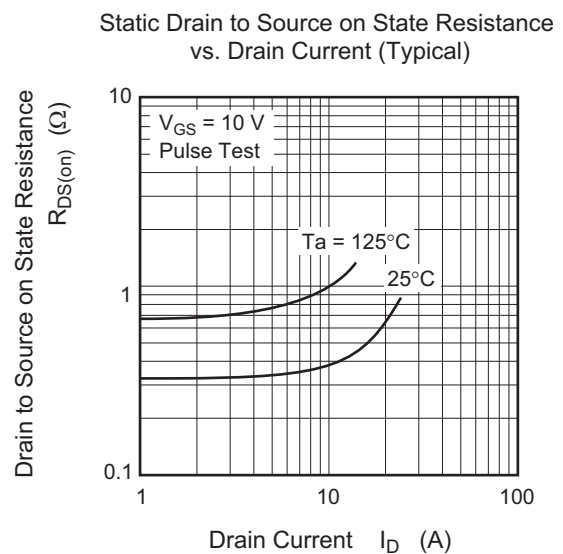
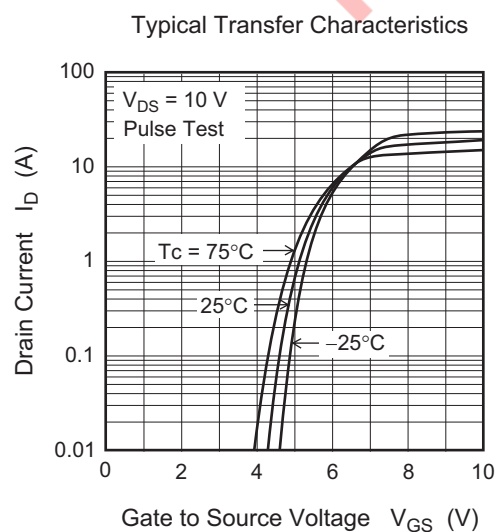
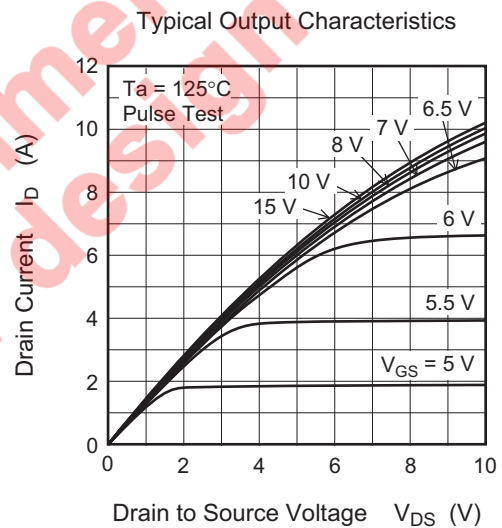
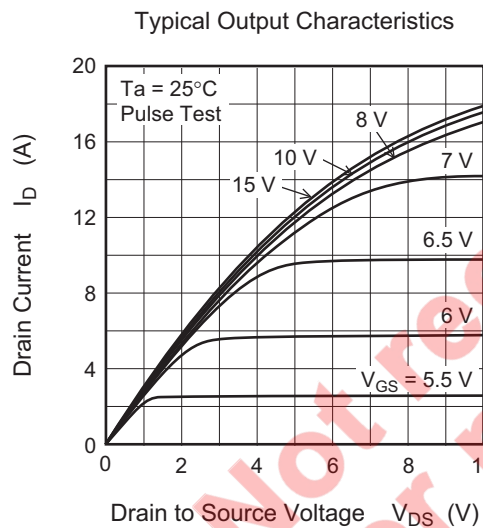
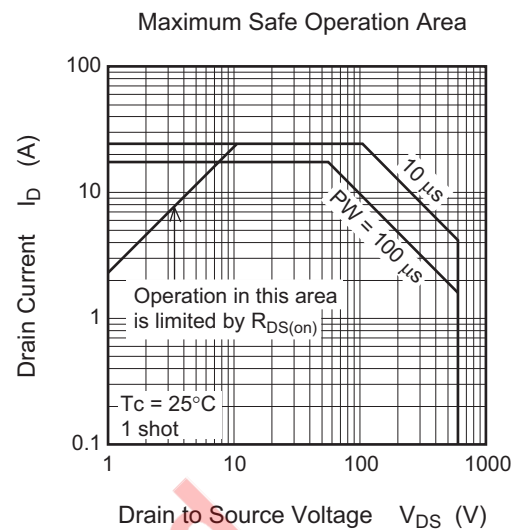
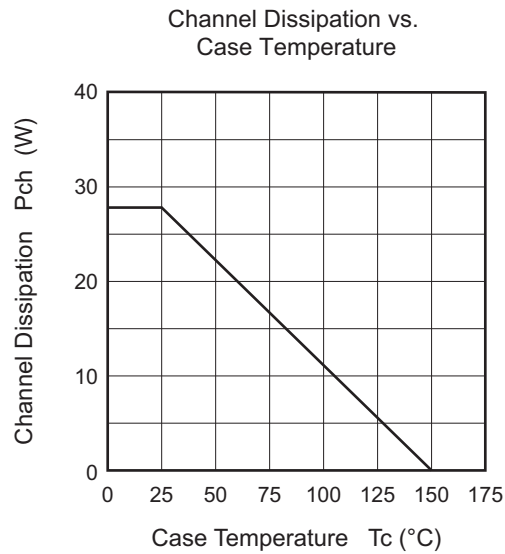
Electrical Characteristics

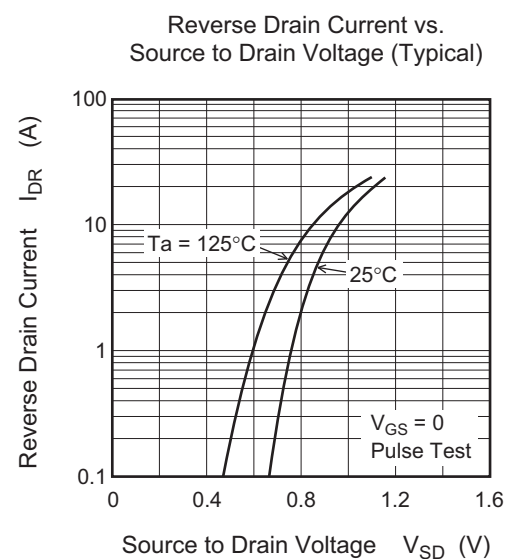
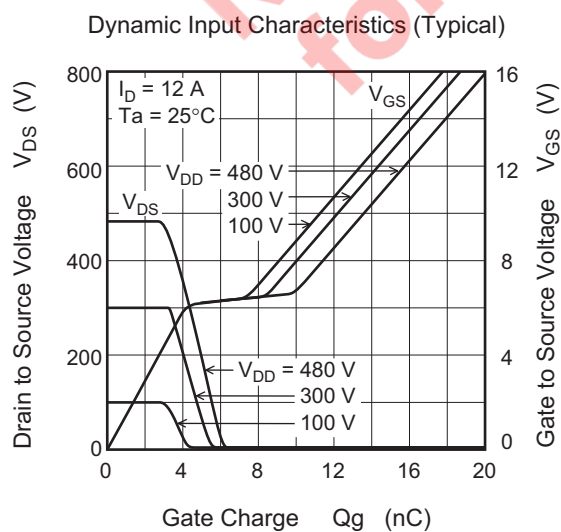
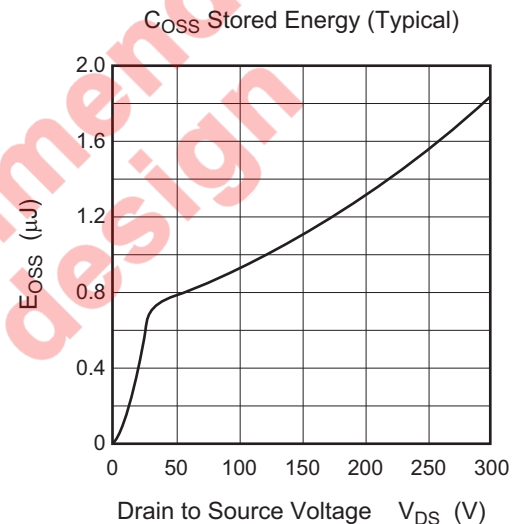
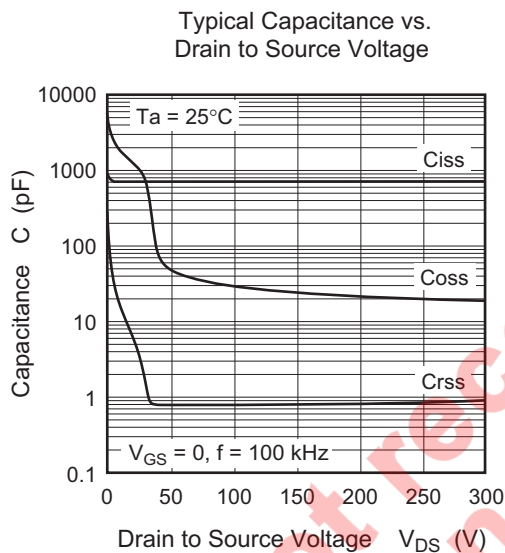
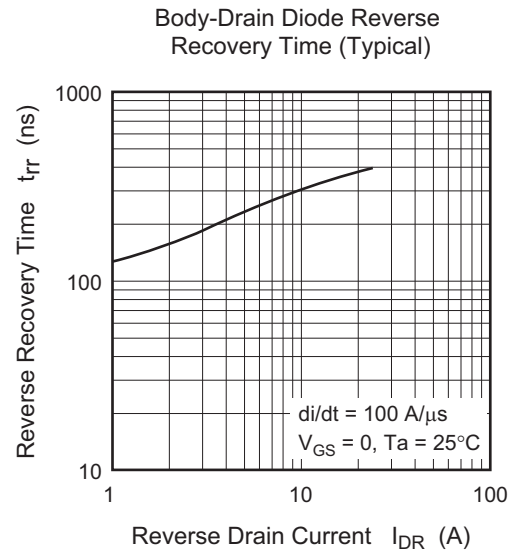
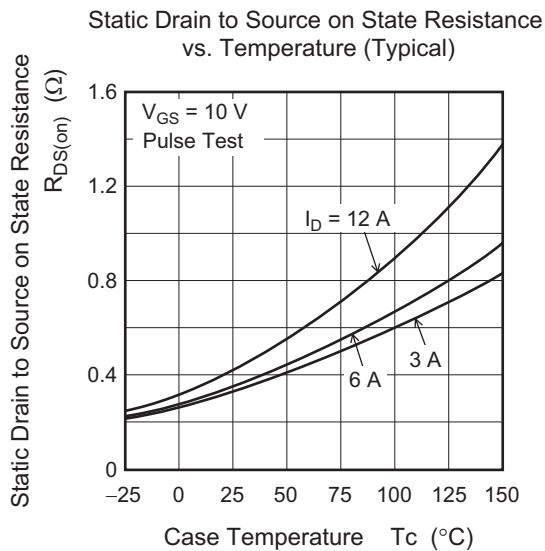
(Ta = 25°C)

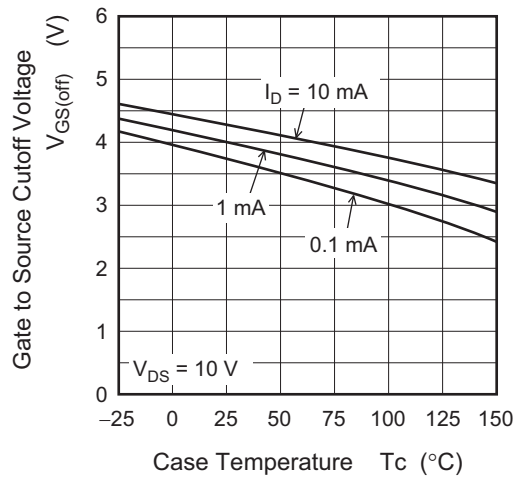
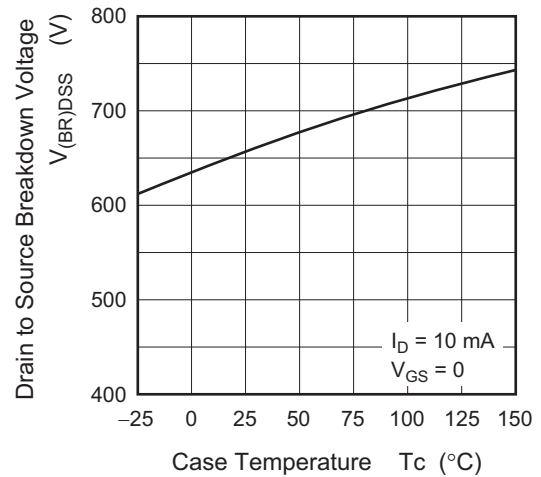
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	600	—	—	V	$I_D = 10 \text{ mA}$, $V_{GS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	1	mA	$V_{DS} = 600 \text{ V}$, $V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 0.1	μA	$V_{GS} = +30\text{V}$, -20 V , $V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	3	—	5	V	$V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.35	0.44	Ω	$I_D = 6 \text{ A}$, $V_{GS} = 10 \text{ V}$ ^{Note5}
	$R_{DS(on)}$	—	0.87	—	Ω	Ta = 150°C $I_D = 6 \text{ A}$, $V_{GS} = 10 \text{ V}$ ^{Note5}
Gate resistance	R_g	—	2.5	—	Ω	f = 1 MHz $V_{DS} = 25 \text{ V}$, $V_{GS} = 0$
Input capacitance	C_{iss}	—	720	—	pF	$V_{DS} = 25 \text{ V}$
Output capacitance	C_{oss}	—	980	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	3.7	—	pF	f = 100 kHz
Turn-on delay time	$t_{d(on)}$	—	13	—	ns	$I_D = 6 \text{ A}$
Rise time	t_r	—	18	—	ns	$V_{GS} = 10 \text{ V}$
Turn-off delay time	$t_{d(off)}$	—	25	—	ns	$R_L = 50 \Omega$
Fall time	t_f	—	18	—	ns	$R_g = 10 \Omega$ ^{Note5}
Total gate charge	Q_g	—	13.6	—	nC	$V_{DD} = 480 \text{ V}$
Gate to source charge	Q_{gs}	—	4.8	—	nC	$V_{GS} = 10 \text{ V}$
Gate to drain charge	Q_{gd}	—	3.9	—	nC	$I_D = 12 \text{ A}$ ^{Note5}
Body-drain diode forward voltage	V_{DF}	—	1.0	1.6	V	$I_F = 12 \text{ A}$, $V_{GS} = 0$ ^{Note5}
Body-drain diode reverse recovery time	t_{rr}	—	320	—	ns	$I_F = 12 \text{ A}$
Body-drain diode reverse recovery current	I_{rr}	—	20	—	A	$V_{GS} = 0$
Body-drain diode reverse recovery charge	Q_{rr}	—	3.7	—	μC	$di_F/dt = 100 \text{ A}/\mu\text{s}$ ^{Note5}

Notes: 5. Pulse test

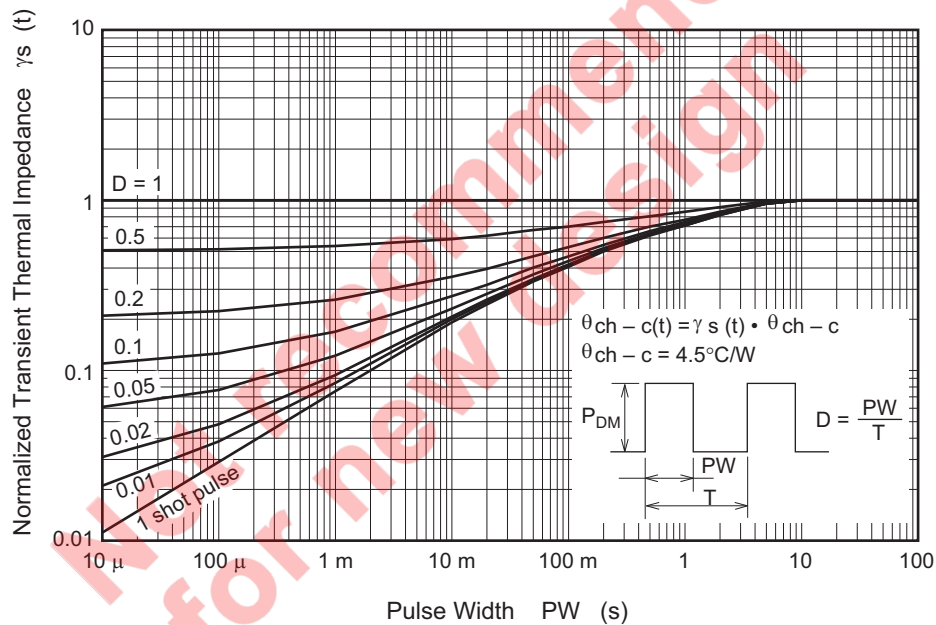
Main Characteristics



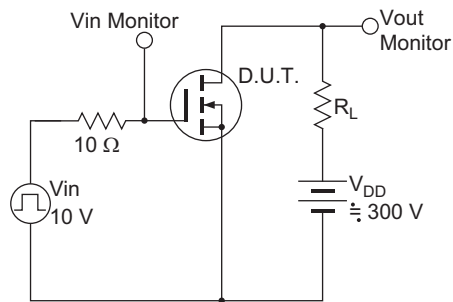


Gate to Source Cutoff Voltage
vs. Case Temperature (Typical)Drain to Source Breakdown Voltage
vs. Case Temperature (Typical)

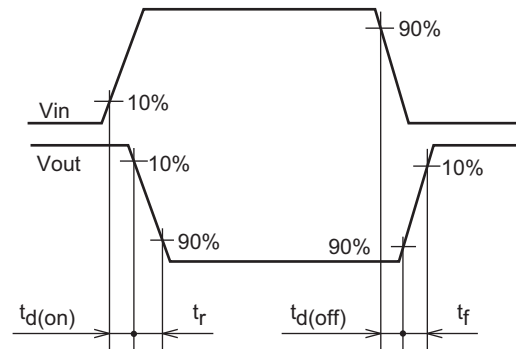
Normalized Transient Thermal Impedance vs. Pulse Width



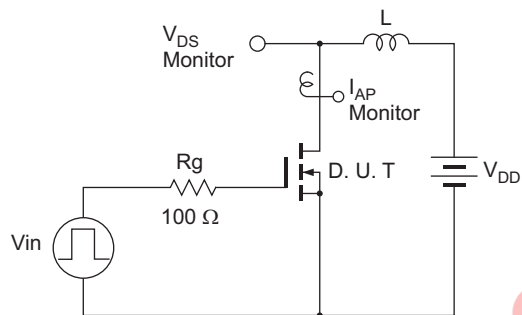
Switching Time Test Circuit



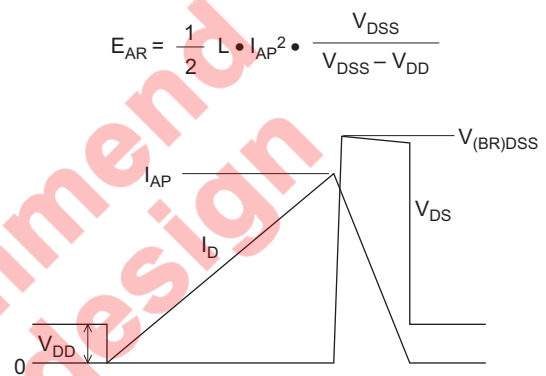
Waveform



Avalanche Test Circuit



Avalanche Waveform



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